Silicon NPN Power Transistors BU102

DESCRIPTION

·With TO-3 package

·$V_{CEO(sus)}$=150V (min)

APPLICATIONS

·Designed for horizontal deflection output stage of CTV receivers

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	400	V
V_{CEO}	Collector-emitter voltage	Open base	150	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		7	A
P_C	Collectorl power dissipation	T_C=25□	100	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=100mA; I_B=0	150			V
$V_{(BR)EBO}$	Emitter-base breakdown votage	I_E=1mA; I_C=0	6			V
$V_{(BR)CBO}$	Collector-base breakdown votage	I_C=1mA; I_E=0	400			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=5 A;I_B=1.0 A			2.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=5 A;I_B=1.0 A			2.5	V
I_{CBO}	Collector cut-off current	V_{CB}=400V; I_E=0			0.1	mA
I_{CEO}	Collector cut-off current	V_{CE}=100V; I_E=0			1.0	mA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			0.1	mA
h_{FE}	DC current gain	I_C=1A ; V_{CE}=5V	30		120	

PACKAGE OUTLINE

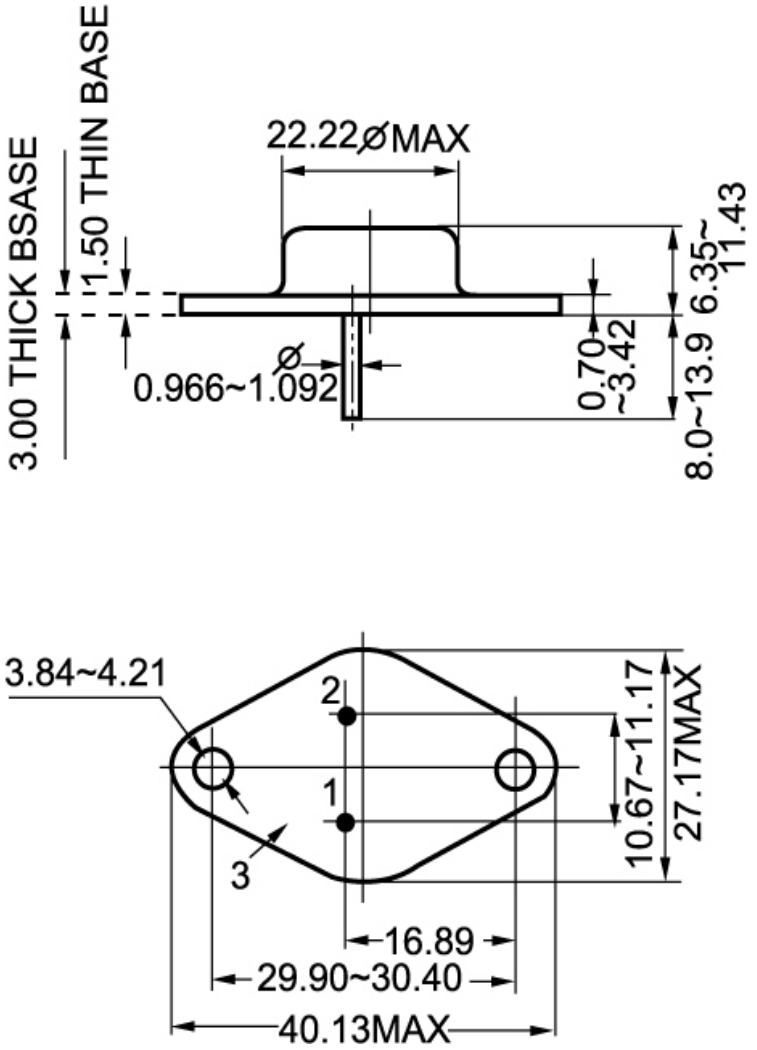


Fig.2 Outline dimensions